



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Bin Yu

Serial No.: 09/826,472

Filed: April 4, 2001

For: Method of Fabricating a Semiconductor Device Having a Nitride/High-K/Nitride Gate Dielectric Stack by Atomic Layer Deposition (ALD) and a Device Thereby Formed

Art Unit: 2812

Examiner: Pompey, Ron Everett

AMENDMENT AND RESPONSE TO FINAL OFFICE ACTION

Mail Stop RCE

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

Dear Sir/Madam:

This is in response to the *Final Office Action* dated October 6, 2003 in the above-referenced patent application. Please enter and consider the following amendments and remarks in light of the attached *Request for Continued Examination* filed under 37 CFR §1.114 in the above-identified application.

In the Attorney Docket No.:

Please replace the old Attorney Docket No. "P1296" with the new Attorney
Docket No. --0180197--.